

REMARKS

Claims 5-18 are pending in the application and stand rejected. By the present amendment, the Title of the Invention and claims 1, 7, and 15 have been amended, and claims 19-24 have been added. The Examiner's reconsideration of the rejection in view of the following remarks and amendments is respectfully requested.

In the Specification:

The Title of the Invention has been amended to accurately describe the invention to which the claims are directed.

Claim Rejection- 35 U.S.C. § 103:

Claims 5-17 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Narui et al. (U.S. Patent 6,150,689) in view of Schnabel et al. (U.S. 6,291,335). Claim 18 is rejected as being unpatentable over Narui and Schnabel as applied to claim 12 above, and further in view of Parekh et al. (U.S. 6,238971).

Although Applicant respectfully disagrees with claim rejections, claim 5 has been amended to include *stud holes are aligned with corresponding one of the first metal contact holes ... and wherein the metal contact studs are formed having a width that is greater than a space between adjacent bit lines.* Further, Applicant believes the amendment to claim 5 places the application in condition for allowance since neither Narui nor Schnabel, singularly or in combination, teach or suggest a method for forming a semiconductor device that comprises, *inter alia, stud holes are aligned with corresponding one of the first metal contact holes... and wherein the metal contact studs are formed having a width that is greater than a space between adjacent bit lines,* as essentially claimed in claim 5.

Claims 6-18 depend from claim 5. As such, these claims are believed to be allowable for at least the same reasons as given for claim 5.

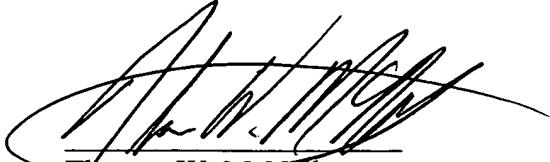
Therefore, withdrawal of the obvious rejections is respectfully requested.

Claims 19-24 have been added to further define the invention. At the very least, Applicant believes that claims 19-24 are allowable over the cited prior art since neither the combination of Narui and Schnabel nor the combination of Narui, Schnabel and Parekh disclose or suggest a method of manufacturing a semiconductor memory device comprising, *inter alia*, *forming lower portions of metal contacts and metal studs in a first insulating layer disposed on a substrate having gate electrodes, wherein each of the metal studs is aligned with corresponding one of the lower portions of the metal contacts... and forming upper portions of the metal contacts that pass through the second and the third insulating layers and in contact with the metal studs...wherein the metal contact studs are formed having a width that is greater than a space between adjacent bit lines*, as essentially claimed in claim 19.

Claims 20-24 depend from claim 19. As such, claims 20-24 are believed to be allowable for at least the same reasons as given above for claim 19.

In view of the foregoing amendment and remarks, it is respectfully submitted that all the claims now pending in the application are in condition for allowance. Early and favorable reconsideration of the case is respectfully requested.

Respectfully submitted,

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